



MMBT3906-AU

PNP GENERAL PURPOSE SWITCHING TRANSISTOR

VOLTAGE 40 Volt **POWER** 330 mWatt

SOT-23 Unit : inch(mm)

FEATURES

- PNP epitaxial silicon, planar design
- Collector-emitter voltage $V_{CE} = -40V$
- Collector current $I_C = -200mA$
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard
- AEC-Q101 qualified

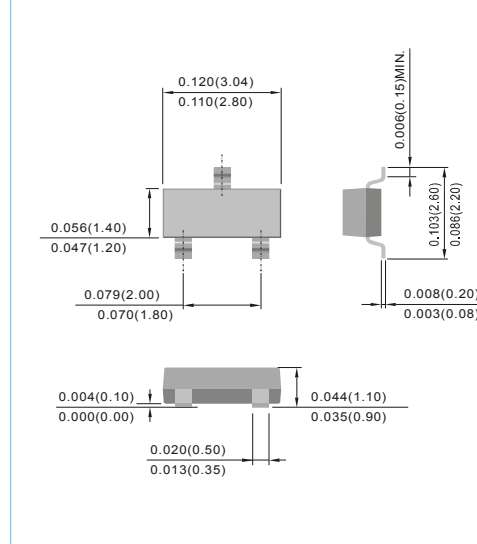
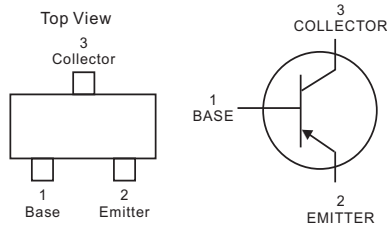
MECHANICAL DATA

Case: SOT-23, Plastic

Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0003 ounces, 0.0084 grams

Marking: S2A



ABSOLUTE RATINGS

Parameter	Symbol	Value	Units
Collector - Emitter Voltage	V_{CEO}	-40	V
Collector - Base Voltage	V_{CBO}	-40	V
Emitter - Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-200	mA

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Units
Max Power Dissipation (Note 1)	P_{TOT}	330	mW
Thermal Resistance , Junction to Ambient	$R_{\theta JA}$	375	$^{\circ}C/W$
Operating Junction Temperature and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^{\circ}C$

Note 1: Transistor mounted on FR-5 board 1 x 0.75 x 0.062 in.



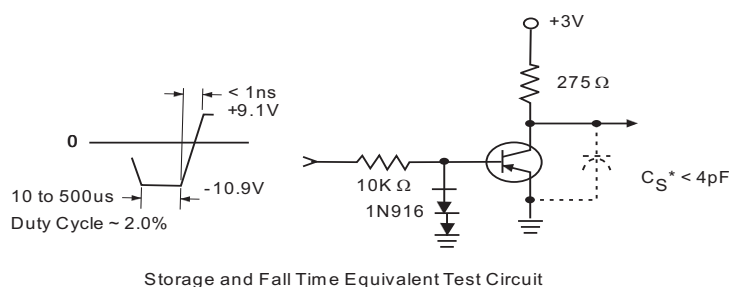
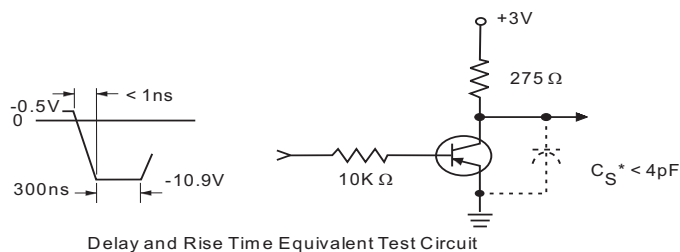
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ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-40	-	-	V
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-40	-	-	V
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5	-	-	V
Base Cutoff Current	I_{BL}	$V_{CE} = -30V, V_{EB} = -3V$	-	-	-50	nA
Collector Cutoff Current	I_{CEX}	$V_{CE} = -30V, V_{EB} = -3V$	-	-	-50	nA
DC Current Gain (Note 2)	h_{FE}	$I_C = -0.1mA, V_{CE} = -1V$	60	-	-	-
		$I_C = -1mA, V_{CE} = -1V$	80	-	-	
		$I_C = -10mA, V_{CE} = -1V$	100	-	300	
		$I_C = -50mA, V_{CE} = -1V$	60	-	-	
		$I_C = -100mA, V_{CE} = -1V$	30	-	-	
Collector - Emitter Saturation Voltage (Note 2)	$V_{CE(SAT)}$	$I_C = -10mA, I_B = -1mA$ $I_C = -50mA, I_B = -5mA$	-	-	-0.25 -0.4	V
Base - Emitter Saturation Voltage (Note 2)	$V_{BE(SAT)}$	$I_C = -10mA, I_B = -1mA$ $I_C = -50mA, I_B = -5mA$	-0.65 -	-	-0.85 -0.95	V
Collector - Base Capacitance	C_{CBO}	$V_{CB} = -5V, I_E = 0, f = 1MHz$	-	-	4.5	pF
Emitter - Base Capacitance	C_{EBO}	$V_{EB} = -0.5V, I_C = 0, f = 1MHz$	-	-	10	pF
Delay Time	t_d	$V_{CC} = -3V, V_{BE} = -0.5V,$ $I_C = -10mA, I_B = -1mA$	-	-	35	ns
Rise Time	t_r	$V_{CC} = -3V, V_{BE} = -0.5V,$ $I_C = -10mA, I_B = -1mA$	-	-	35	ns
Storage Time	t_s	$V_{CC} = -3V, I_C = -10mA$ $I_{B1} = I_{B2} = -1mA$	-	-	225	ns
Fall Time	t_f	$V_{CC} = -3V, I_C = -10mA$ $I_{B1} = I_{B2} = -1mA$	-	-	75	ns
Current Gain-Bandwidth Product	f_T	$I_C = -10mA, V_{CE} = -20V,$ $f = 100MHz$	250	-	-	MHz

Note 2: Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2.0\%$.

SWITCHING TIME EQUIVALENT TEST CIRCUITS





ELECTRICAL CHARACTERISTICS CURVE

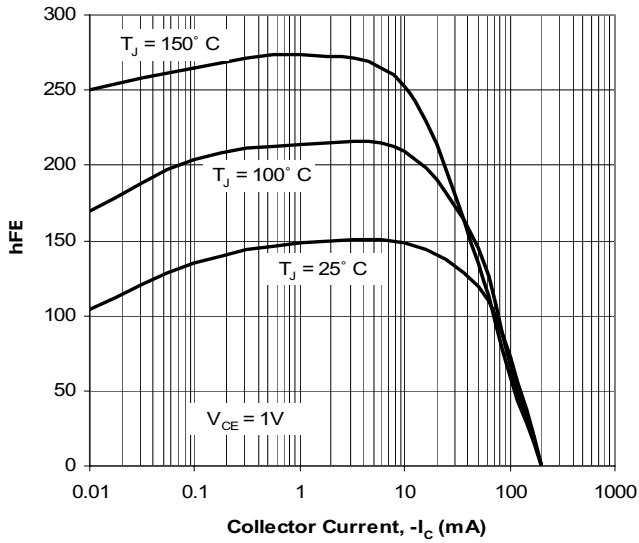


Fig. 1. Typical h_{FE} vs. Collector Current

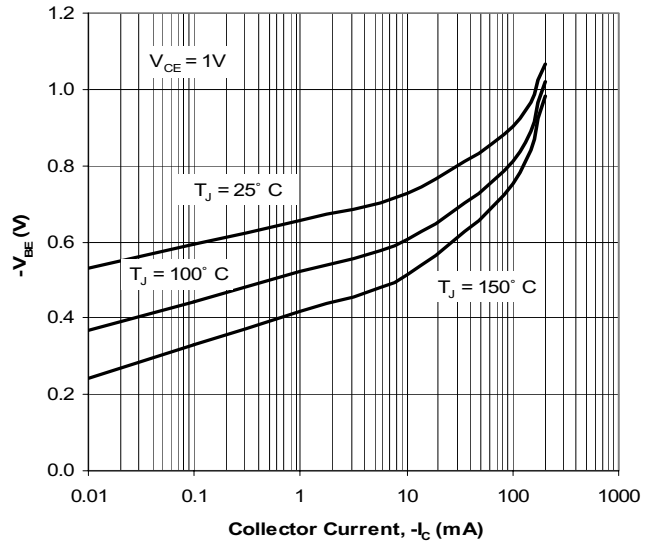


Fig. 2. Typical V_{BE} vs. Collector Current

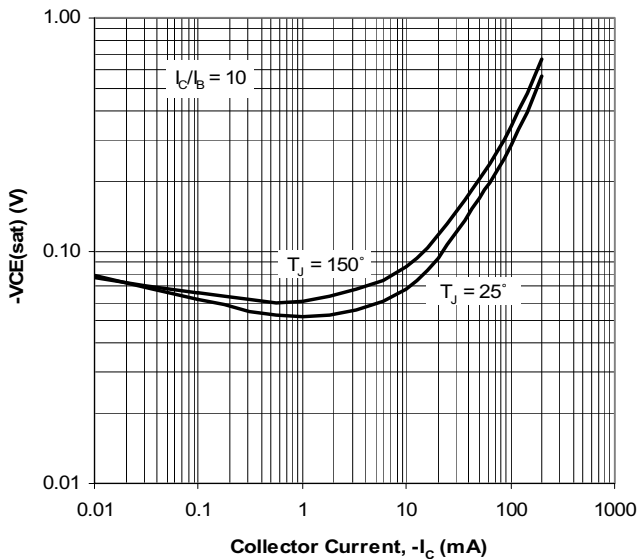


Fig. 3. Typical $V_{CE(sat)}$ vs. Collector Current

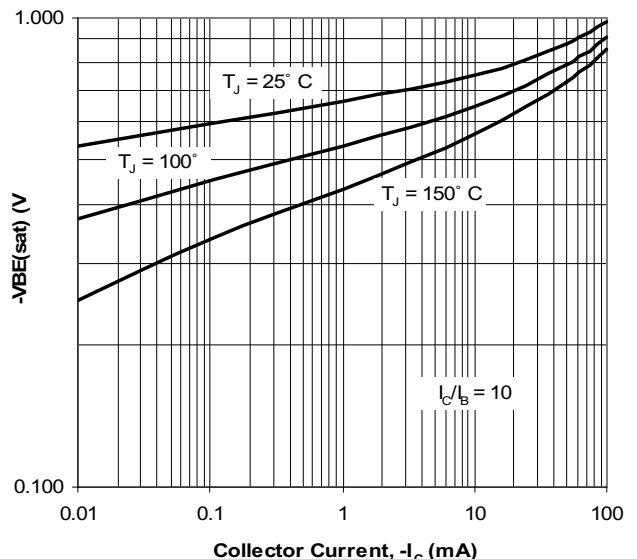


Fig. 4. Typical $V_{BE(sat)}$ vs. Collector Current

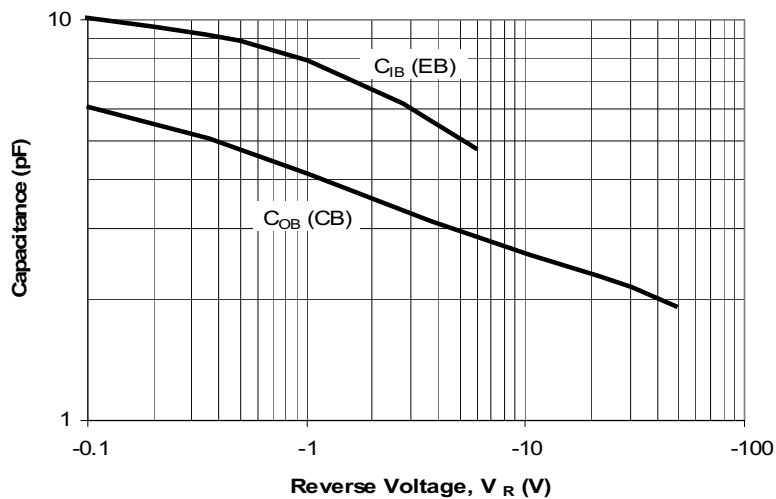


Fig. 5. Typical Capacitances vs. Reverse Voltage

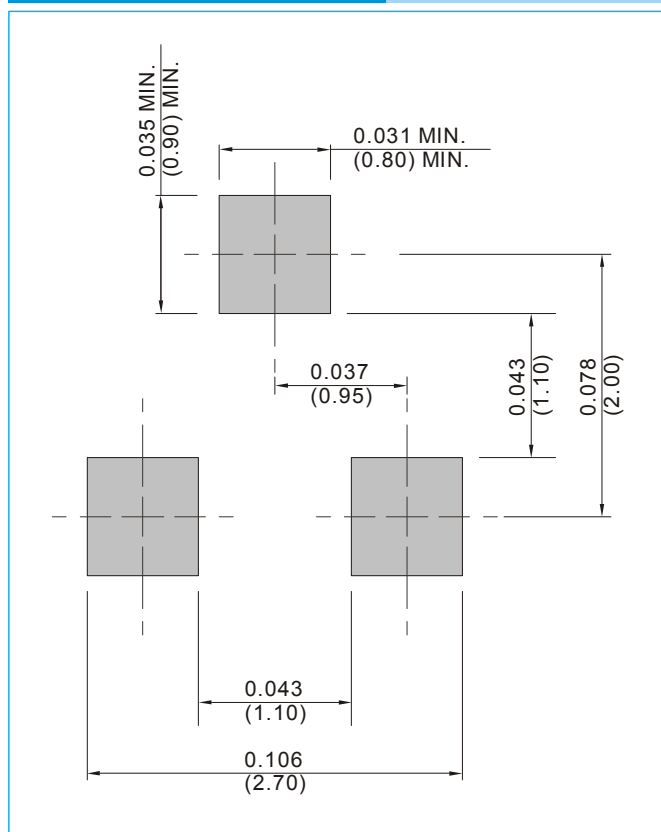


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MOUNTING PAD LAYOUT

SOT-23

Unit : inch(mm)



ORDER INFORMATION

- Packing information
T/R - 12K per 13" plastic Reel
T/R - 3K per 7" plastic Reel



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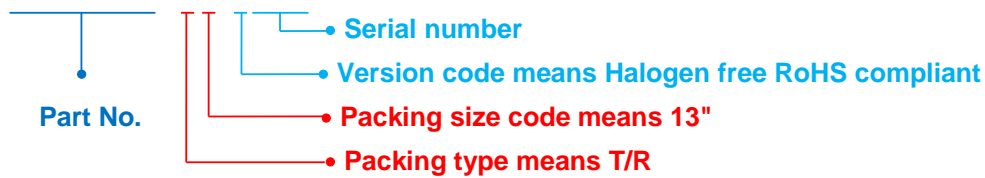
Part No. _packing code_ Version

MMBT3906-AU_R1_000A1

MMBT3906-AU_R2_000A1

For example :

RB500V-40_R2_00001



Packing Code XX				Version Code X		Serial number XXXX
Packing type	1 st Code	Packing size code	2 nd Code	HSF Level	1 st Code	2 nd ~5 th Code
Tape and Ammunition Box (T/B)	A	N/A	0	Halogen free RoHS compliant	0	serial number
Tape and Reel (T/R)	R	7"	1	RoHS compliant	1	serial number
Bulk Packing (B/P)	B	13"	2			
Tube Packing (T/P)	T	26mm	X			
Tape and Reel (Right Oriented) (TRR)	S	52mm	Y			
Tape and Reel (Left Oriented) (TRL)	L	PANASERT T/B CATHODE UP (PBCU)	U			
FORMING	F	PANASERT T/B CATHODE DOWN (PBCD)	D			